IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A semiconductor laser device, comprising:

a semiconductor laser element arranged inside an airtight-sealed package, the semiconductor laser element having an active region formed of a gallium nitride-based crystal,

wherein a rated output power of the semiconductor laser device is 30 mW or more, and an atmospheric gas inside the package is a mixture of oxygen and nitrogen, with an oxygen content of more than 20%, and the semiconductor laser device has a mean time to failure (MTTF) of 3,000 hours or more at 70°C.

2. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element has a dielectric oxide film formed on a laser emission surface thereof.

3. (Cancelled)

4. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element emits light having a wavelength of 0.9 μm or less.

5. (Previously Presented) The semiconductor laser device of claim 1, wherein the atmospheric gas inside the package is dry air.

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (Previously Presented) The semiconductor laser device of claim 1, wherein the gallium nitride-based crystal is an AlGaN- or InGaN-based crystal.